

SOT-23 Formed SMD Package

CSA1362

LOW FREQUENCY POWER AMPLIFIER TRANSISTOR

P-N-P transistor

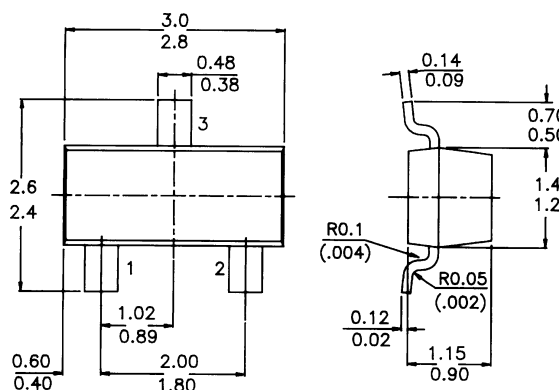
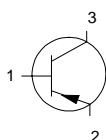
Marking

CSA1362GR = 62

PACKAGE OUTLINE DETAILS ALL DIMENSIONS IN mm

Pin configuration

1 = BASE
2 = EMITTER
3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	15 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	800 mA
Total power dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	max	200 mW
Junction temperature	T_j	max.	150 °C
D.C. current gain			
$-I_C = 100 \text{ mA}; -V_{CE} = 1 \text{ V}$	h_{FE}	min.	120
		max.	400

RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	15 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	800 mA
Total power dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	max	200 mW

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Storage temperature	T_{stg}	-55 to +150 °C
Junction temperature	T_j	max. 150 °C

THERMAL CHARACTERISTICS

$$T_j = P (R_{th\ j-t} + R_{th\ s-a}) + T_{amb}$$

Thermal resistance

from junction to ambient	$R_{th\ j-a}$	556 °C/mW
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CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Collector-emitter breakdown voltage

$-I_C = 10\text{ mA}$	$-V_{(BR)CEO\ min.}$	15 V
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Collector cut-off current

$-V_{CB} = 15\text{ V}$	$-I_{CBO}$	max. 100 nA
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Emitter cut-off current

$V_{EB} = 5\text{ V}$	I_{EBO}	max. 100 nA
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Saturation voltages

$-I_C = 400\text{ mA}; -I_B = 8\text{ mA}$	$-V_{CEsat}$	max. 0.25 V
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Base Emitter on voltage

$I_C = 10\text{ mA}, V_{CE} = 1\text{ V}$	$-V_{BE(on)}$	min. 0.5 V
		max. 0.8 V

D.C. current gain

$I_C = 100\text{ mA}; -V_{CE} = 1\text{ V}$	h_{FE}	min. 120
		max. 400

Y	min. 120
	max. 240

GR	min. 200
	max. 400

$I_C = 800\text{ mA}; V_{CE} = 1\text{ V}$		min. 40
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Transition frequency

$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$	f_T	typ. 120 MHz
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Collector output capacitance

$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	C_{ob}	typ. 13 pF
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[查询"CSA1362"供应商](#)

Disclaimer

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